Abstracts

Hot-Electron-Induced Degradation of Pseudomorphic High-Electron Mobility Transistors

Y.A. Tkachenko, C.J. Wei, J.C.M. Hwang, T.D. Harris, R.D. Grober, D.M. Hwang, L. Aucoin and S. Shanfield. "Hot-Electron-Induced Degradation of Pseudomorphic High-Electron Mobility Transistors." 1995 Microwave and Millimeter-Wave Monolithic Circuits Symposium Digest 95.1 (1995 [MCS]): 115-118.

Pseudomorphic high-electron mobility transistors have been found to undergo hot-electron-induced degradation. Due to the negative temperature dependence of hot-electron effects, it will be necessary to conduct electrical and temperature stress tests separately, in order to ascertain the reliability of these transistors under normal operating conditions.

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